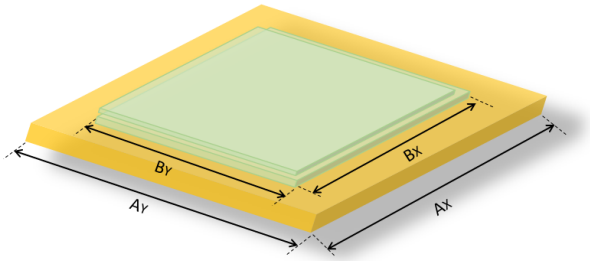
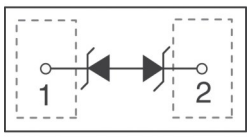
FM-05VR6T10

Chip TVS diode





Mechanical Data	Notes
Dice size	AX:330um,AY:330um,BX:150um,BY:150um
Wafer size	6”(good die:139,000pcs)
Chip Thickness	165um(max)
Scribe line width	50um
Top metal	Ti-Ni-Ag
Back side metal	Ti-Ni-Ag for soldering

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	V_{RWM}		5	V
Peak pulse power	P_{PP}	tp=8/20us	75	W
Peak pulse current	I_{PP}	tp=8/20us	5	A
Electrostatic discharge	V_{ESD}	IEC61000-4-2	± 25(AIR)	KV
Max.junction temp.	Tj		+150	℃

Characteristics TA=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown Voltage	V_{BR}	I_T=1mA	6.1		8.5	V
Reverse leakage current	I_R	V_R=5V			0.03	uA
Clamping voltage	Vc	I_{PP}=1A I_{PP}=5A			9.0 15.0	V
Diode capacitancd pin1 to 2	Cj	V_R=0V f=1MHz	8.0	10.0	13.0	pf

Notes:

(1)sampling testing:no bad dice inking/guaranteed good die >93%

(2)Testing follow customer

(3)Tj=Ta+Rth(j-a)*(pf+pr),where Rth(j-a)-thermal resistance,Pf-forward power dissipation, Pr-revers power dissipation

(4)**For device testing